

EAST - [t0785310 trench NROM w/ p-1]

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Actice

- ↳ L1: (159381) (nrom read adj only adj memory)
- ↳ L2: (1110/785310)
- ↳ L3: (231318) (sonos monos mnos nrom nitride adj3 memory)
- ↳ L4: (771) (nrom)
- ↳ L5: (998) (nrom volatile non adj volatile adj read adj only)
- ↳ L6: (714 with 5)
- ↳ L7: (8932) (nrom nitride adj read adj only adj memory)
- ↳ L8: (991) (nitride adj read adj only adj memory)
- ↳ L9: (992) (nitride adj read adj only)
- ↳ L10: (322) 9 with 4
- ↳ L11: (88825) trench\$9
- ↳ L12: (822) 9 4
- ↳ L13: (32) 11 with 12
- ↳ L14: (46) 11 same 12
- ↳ L15: (7852821) (select\$4 side control adj (gate line) \$6
- ↳ L16: (77) 14 and 16
- ↳ L17: (168) 11 and 12
- ↳ L18: (684490) (select\$4 side 1 adj (gate line) \$6
- ↳ L19: (68) 17 and 18
- ↳ L20: (1251684) group\$3
- ↳ L21: (21) 12 with 20
- ↳ L22: (2) 12 same 20
- ↳ L23: (1559) nor adj memory
- ↳ L24: (4) 23 with 11
- ↳ L25: (151) 23 same 11

29 same 11

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#	Inventor	Document Issue P.	Title	Current Current I. Retirev	S	C	P	Image	Def
1	Ding, Yi	US 200500 2005 3	Fabrication of conductive gates for non	438/25 438/268	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20050
2	Ding, Yi	US 200402 200413	Fabrication of dielectric on a gate surf	438/58 438/197	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20040
3	Ding, Yi	US 200402 200413	FABRICATION OF GATE DIELECTRIC IN NOR	438/25	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20040
4	Ding, Yi	US 200402 200413	FABRICATION OF GATE DIELECTRIC IN NOR	25/7/31	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20040
5	Ding, Yi	US 200402 200413	NOR VOLATILE MEMORIES WITH A FLOATING	25/7/31 297/316	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20040
6	Ding, Yi	US 2004018 2004 47	Nonvolatile memories and methods of	438/25 438/268	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 200401
7	Ding, Yi	US 2004018 2004 5	Nonvolatile memories and methods of	438/25 257/316	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 200401
8	Ding, Yi	US 2004018 2004 4	Fabrication of integrated circuit elem	438/25	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 200401
9	Forbes, Leo	US 200502 2005 2	Nor flash memory cell with high storag	365/18	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20050
10	Li Chi Han &	US 200201 2002 11	Non-volatile memory with a serial tran	257/28 257/E27.10	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 200201